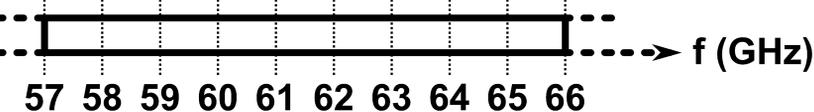


# A Characterization Method of On-Chip Tee-Junction for Millimeter-Wave CMOS Circuit Design

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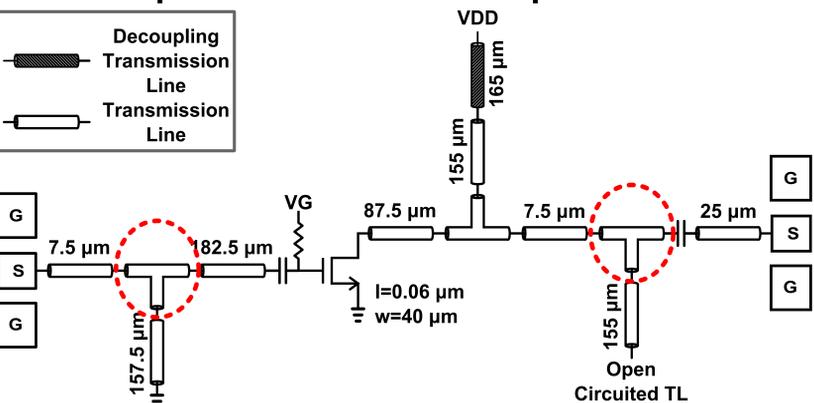
## 1. Motivation



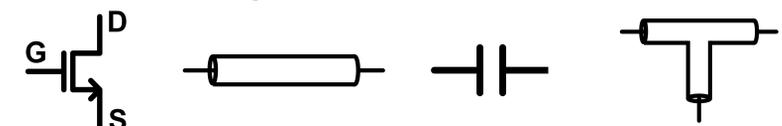
• 60-GHz wireless communication with 9 GHz unlicensed bandwidth

- Wide bandwidth: 2.16 GHz x 4 channels
- Ultra high data rate: 64QAM → 10.56Gbps/ch  
64QAM → 42.24Gbps (4-ch bonding)

• An example millimeter-wave amplifier

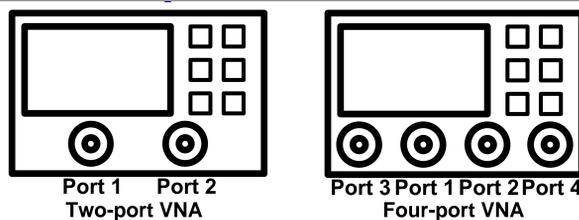


• Several active/passive devices to be modeled

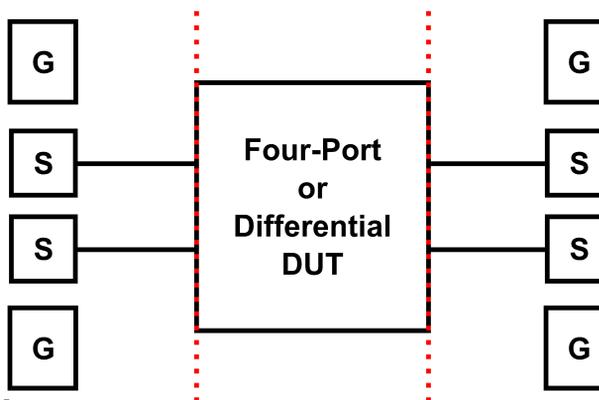


• This work focus on Tee-Junction characterization

## 2. Multi-port measurements



- Most common VNAs
- More dynamic range than multi-port
- More accurate measurements

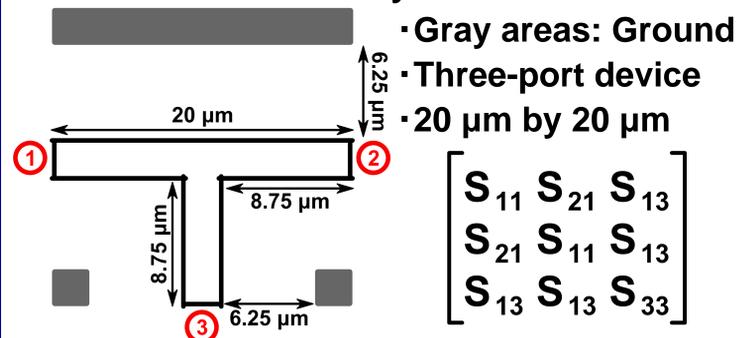


Issues:

- De-embedding of pad parasitics
- Unwanted crosstalk and coupling
- Fabrication of more structures
- Increased area and cost

## 3. Tee-junction and structures

• Tee-Junction Geometry

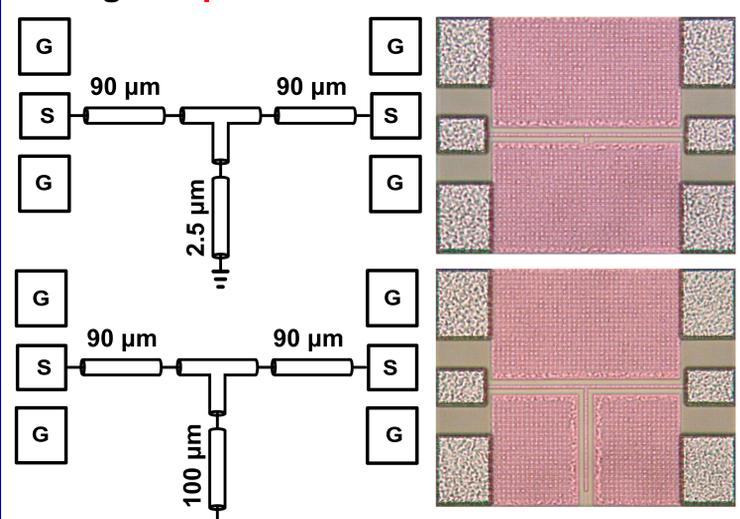


- Gray areas: Ground
- Three-port device
- 20 μm by 20 μm

$$\begin{bmatrix} S_{11} & S_{21} & S_{13} \\ S_{21} & S_{11} & S_{13} \\ S_{13} & S_{13} & S_{33} \end{bmatrix}$$

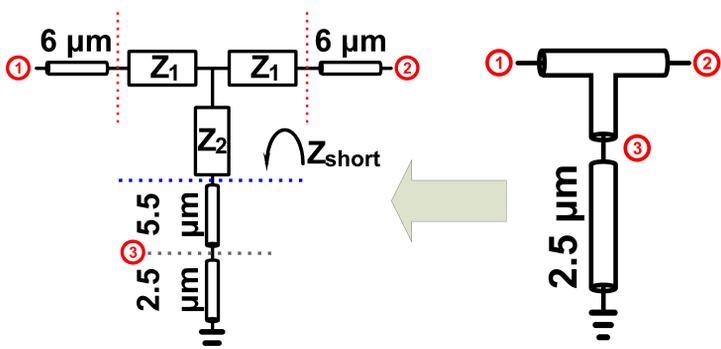
• Two characterization structures

• Using two-port measurements

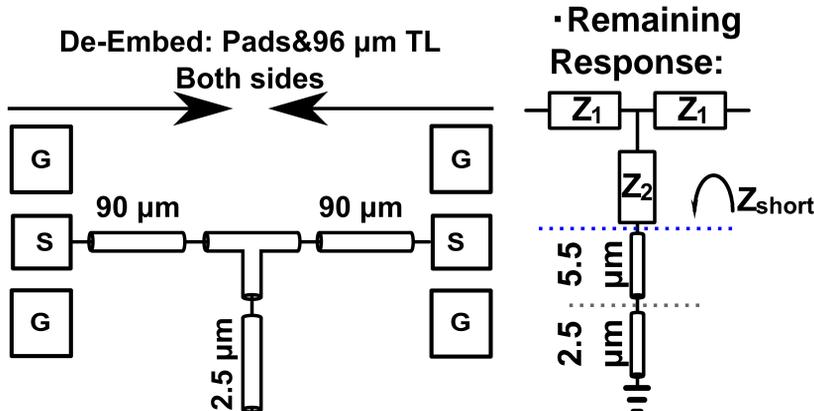


## 4. Characterization method

• Tee-Junction Model



• From the measurement results of the following structure;



$$Z_{\text{de-embed}} = \begin{bmatrix} Z_{11} & Z_{21} \\ Z_{21} & Z_{11} \end{bmatrix} = \begin{bmatrix} Z_1 + Z_2 + Z_{\text{short}} & Z_2 + Z_{\text{short}} \\ Z_2 + Z_{\text{short}} & Z_1 + Z_2 + Z_{\text{short}} \end{bmatrix}$$

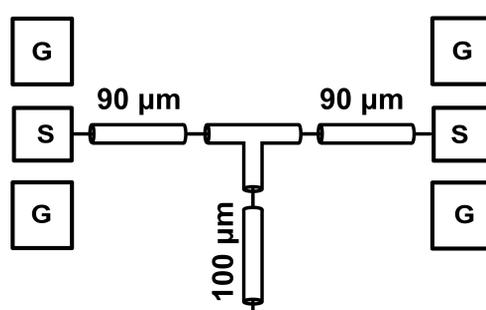
• Lumped constants can be calculated as:

$$Z_1 = Z_{11} - Z_{21}$$

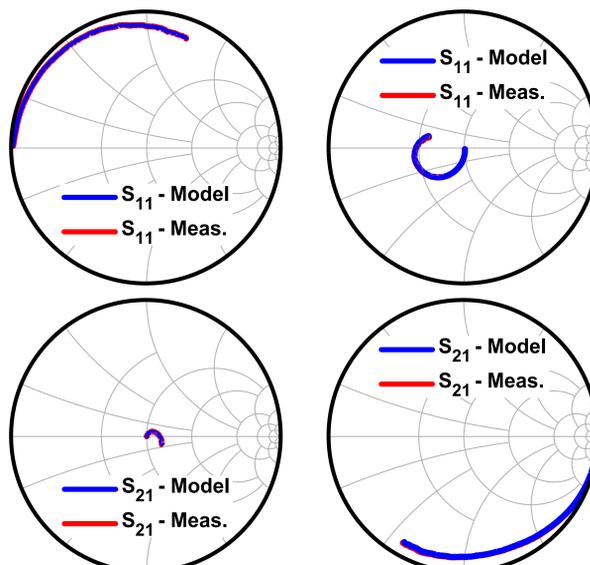
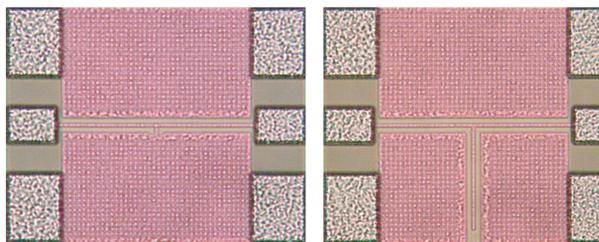
$$Z_2 = Z_{21} - Z_{\text{short}}$$

## 5. Measurement results

• Verification structure with shunt open circuited transmission line.

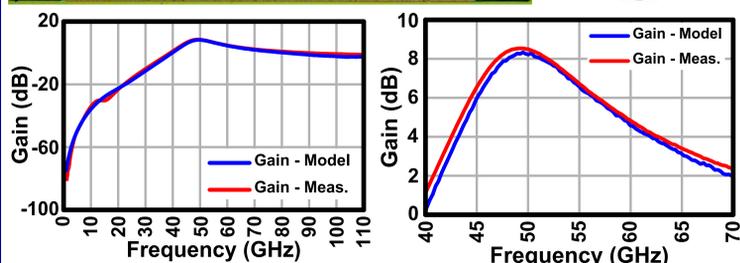
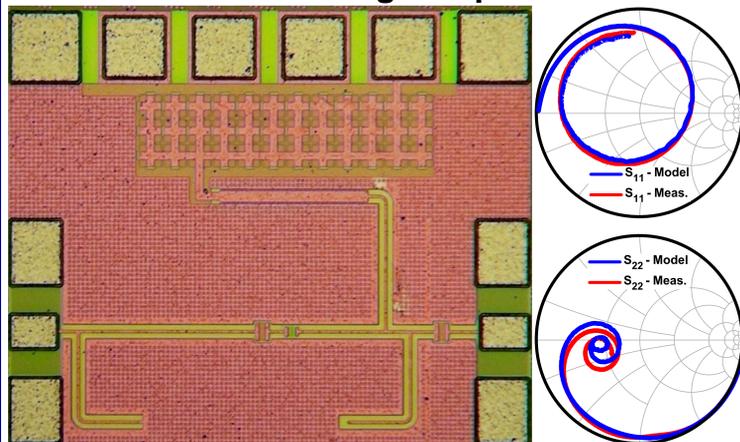


• Measurement and model comparisons



## 6. Application on one-stage amp.

• Manufactured one-stage amplifier:



## 7. Conclusions

- A simple characterization approach
- Two-port measurements are used
- Model based on lumped constants and transmission lines
- Z-parameters are used for lumped constant
- Model and measurement results agree well up to 110 GHz
- Application on one-stage amplifier
- Amplifier measurement and model agree well up to around 80 GHz